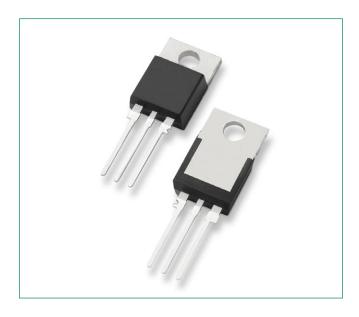


MCR310





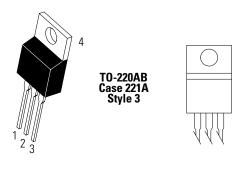
Description

Designed for industrial and consumer applications such as temperature, light and speed control; process and remote controls; warning systems; capacitive discharge circuits and MPU interface.

Features

- Center Gate Geometry for Uniform Current Density
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Low Trigger Currents, 200 µA Maximum for Direct Driving from Integrated Circuits
- Pb–Free Packages are Available

Pin Out



Functional Diagram



Additional Information







Samples

Thyristors Surface Mount -400 - 800V > MCR310

Maximum Ratings (T_J = 25°C unless otherwise noted)

Rating	Part Number	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) $(T_J = -40 \text{ to } +125^{\circ}\text{C}, \text{ Gate Open})$	MCR310-6 MCR310-8 MCR310-10	V _{DRM} ,	400 600 800	V
On-State RMS Current (T _c = 75°C)		I _{T (RMS)}	10	А
Peak Non-Repetitive Surge Current (1/2 Cycle, 60 Hz, T _J = -40 to 110°C)		I _{TSM}	100	А
Circuit Fusing (t = 8.3 ms)		l²t	40	A ² sec
Peak Gate Voltage (t ≤ 10 µs)		V _{GM}	±5	V
Peak Gate Current (t ≤ 10 μs)		I _{GM}	1	А
Peak Gate Power (t ≤ 10 µs)		Р _{дм}	5	W
Average Gate Power		P _{G (AV)}	0.75	W
Operating Junction Temperature Range		T _J	-40 to +110	°C
Storage Temperature Range		T _{stg}	-40 to +150	°C
Mounting Torque		-	8.0	in. lb.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating

Thermal Characteristics

Characterstic	Symbol	Value	Unit	
Thermal Resistance, Junction-to-Case	R _{euc}	2.2		
Thermal Resistance, Junction-to-Ambient	R _{eJA}	60		

Electrical Characteristics ($T_c = 25$ °C, $R_{gK} = 1 \text{ k}\Omega$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Forward Blocking Current (Note 1)	T _C = 110°C	- I _{DRM}	-	-	500	μА
$(T_J = 110^{\circ}C, V_D = Rated V_{DRM})$	T _C = 25°C		_	_	10	
Peak Reverse Blocking Current (Note 1)	T _C = 110°C	I _{RRM} —	-	_	500	μА
$(T_J = 110^{\circ}C, V_R = Rated V_{DRM})$	T _C = 25°C		-	_	10	
On-State Voltage (I _{TM} = 20 A Peak, Pulse Width ≤ 1 ms, Duty Cycle ≤ 2%)		V _{TM}	-	1.7	2.2	V
Gate Trigger Current Continuous dc (Note 2) ($V_D = 12 \text{ Vdc}$, $R_L = 100 \Omega$)		I _{GT}	-	30	200	μΑ
Gate Trigger Voltage, Continuous dc $(V_D = Rated V_{DRM}, R_L = 10 k\Omega, T_J = 110$ °C)		V _{GT}	- 0.1	0.5	1.5 -	mA
Holding Current ($V_D = 12 \text{ V}$, $I_{TM} = 100 \text{ mA}$)		I _H	-	-	6	mA
Critical Rate of Rise of Forward Blocking Voltage $(V_D = Rated V_{DRM'} T_J = 110^{\circ}C, Exponential Waveform)$		dv/dt	-	10	_	V/µs
Gate Controlled Turn-On Time $(V_D = Rated V_{DRM'} I_{TM} = 20 A, I_G = 2 mA)$		t _{gt}	-	1	_	μs

^{1.} Ratings apply for negative gate voltage or RGK = 1 $k\Omega$. Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Devices should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.

Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

^{2.} Does not include RGK current.



Figure 1. Typical RMS Current Derating

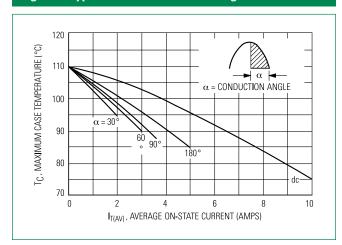


Figure 2. Peak Capacitor Discharge Current Derating

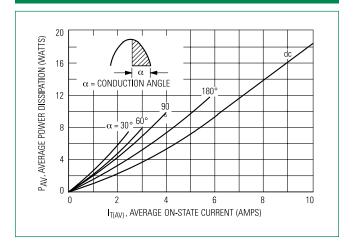


Figure 3. Current Derating

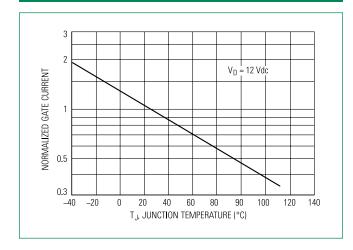
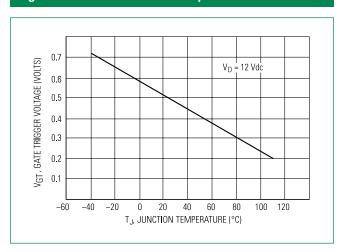
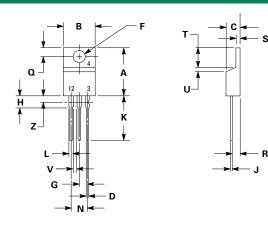


Figure 4. Maximum Power Dissipation

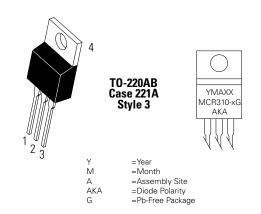




Dimensions



Part Marking System



Di	Dim Inches Max		Millin	neters Max	
DIM			Min		
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
K	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
N	0.195	0.205	4.95	5.21	
Q	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
s	0.045	0.060	1.14	1.52	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z	_	0.080		2.04	

Pin Assignment		
1	Cathode	
2	Anode	
3	Gate	
4	Anode	

Ordering Information

Device	Package	Shipping
MCR310-6	TO-220AB	
MCR310-6G	TO-220AB (Pb-Free)	
MCR310-8	TO-220AB	
MCR310-8G	TO-220AB (Pb-Free)	500 Units / Box
MCR310-10	TO-220AB	
MCR310-10G	TO-220AB (Pb-Free)	

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